

DESCRIPTION

The AP8012 combines a dedicated current mode PWM controller with a high voltage power MOSFET on the same silicon chip.

Typical Power Capability:

Type	SOP8	DIP8
European (195-265 Vac)	W8	13W
US (85-265 Vac)	5 W	W8

The AP8012 is available in SOP8 and DIP8 package.

ORDERING INFORMATION

Package Type	Part Number			
		AP8012M8U		
SOP8	M8	AP8012M8R		
3076		AP8012M8VU		
		AP8012M8VR		
DIP8	DIP8 P8	AP8012P8U		
DIFO	го	AP8012P8VU		
Note	R: Tape & Reel			
NOLE	V: Green Package			

AiT provides all Pb free products Suffix "V" means Green Package

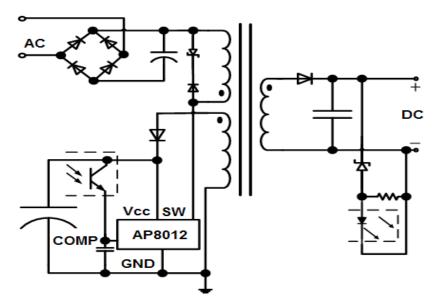
FEATURES

- 85v to 265v wide range AC voltage input
- A 700v MOSFET on the same silicon chip
- Auto start up with high voltage current source
- PWM with current mode control
- 9v to 38v wide range VCC voltage
- Fixed 60KHz switching frequency
- Automatic skip cycle mode in low load condition.
- Over temperature, over current and over voltage protection
- Auxiliary under voltage lockout with hysteresis
- Available in SOP8 and DIP8 Package

APPLICATION

- Power AC/DC Adapters for Chargers
- DVD/VCD power supplies
- Electromagnetic Oven power supplies
- Air Conditioner power supplies
- STB power supplies
- AC/DC LED Driver Applications

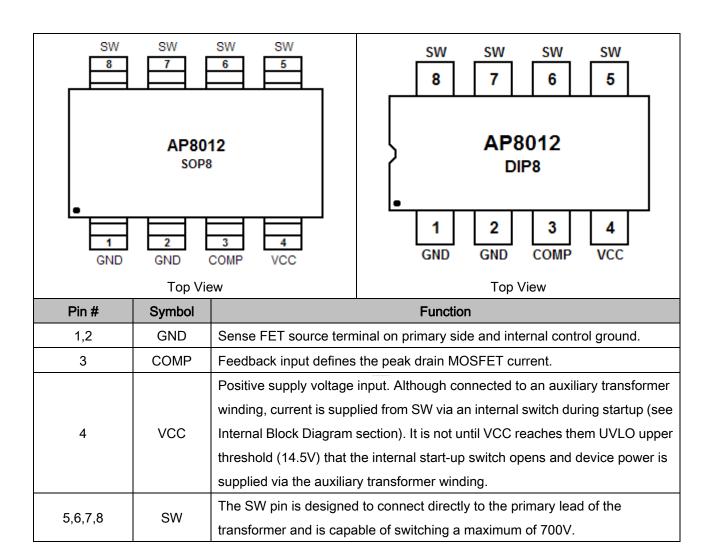
Typical Application



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PIN DESCRIPTION



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ABSOLUTE MAXIMUM RATINGS

(T_A=25°C, unless otherwise specified)

•	• • •		
Vsw	SW to GND Voltage (T _j =25-125°C)	-0.3 to 730	V
I _D	Continuous VDMOS Drain Current	Internally limited	Α
VCC	Supply Voltage	0 to 50	V
Ісомр	Feedback Current	3	mΑ
VESDMM	Electrostatic Discharge:	200	
	Machine Model ((R=0Ω; C=200pF)	200	V
V _{ESDHBM}	Electrostatic Discharge: HBM	2000	V
Tj	Junction Operating Temperature	Internally limited	°C
Tc	Case Operating Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

Power

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
BV _{DSS}	VDMOS Broakdown Voltago	I _D =1mA;	730			V
DVDSS	VDMOS Breakdown Voltage	V _{COMP} =2V	730			V
	Zara Cata Valtaria Drain Commant	V _{DS} =500V;			400	
IDSS	Zero Gate Voltage Drain Current	V _{COMP} =2V;			100	μA
В	Static Dunin Course on Bosistano	V _{GS} =10V		07	20	
R _{DSON}	Static Drain-Source on Resistance	I _D =0.4A;		27	30	Ω
_	Dia a Tima	I _D =0.1A;		50		
Tr	Rise Time	V _{IN} =300V		50		
Tf	Fall Time	I _D =0.2A;		100		ns
		V _{IN} =300V				
Coss	VDMOS Drain Capacitance	V _{DS} =25V		40		рF

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GREEN POWER



Control

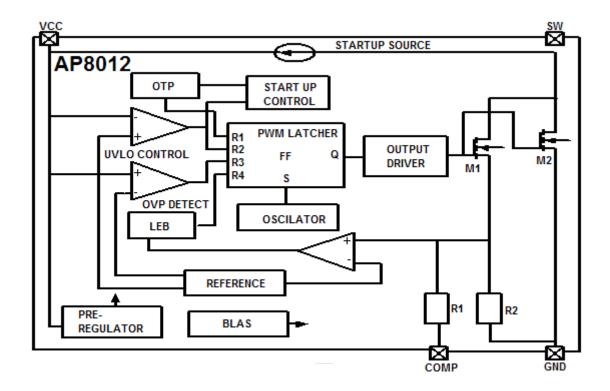
(T_A=25°C, VCC=18V, unless otherwise specified)

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
UVLO SE	CTION		•	•	•	
V _{START}	VCC Start Threshold Voltage	V _{COMP} =0V	13	14.5	16	V
VSTOP	VCC Stop Threshold Voltage	V _{COMP} =0V	7	8	9	V
V _{HYS}	VCC Threshold Hysteresis		5.8	6.5	7.2	V
OSCILLAT	FOR SECTION		l	l		
		V _{STOP} ≤VCC≤35V;	54	60	66	kHz
Fosc	Initial Accuracy	0≤T _j ≤ 100°C				
ΔF/ΔΤ	Frequency Change With Temperature	-25°C ≤ T _j ≤ +85°C		±5	±10	%
FEEDBAC	K SECTION				JI.	
		Tj=25°C,				
Ісомр	Feedback Shutdown Current	V _{COMP} = 0V		0.9		mA
RCOMP	COMP Pin Input Impedance	ID=0mA		1.2		kΩ
CURRENT	LIMIT(SELF-PROTECTION)SECTIO	N			•	
G _{ID}	I _{COMP} to I _D Current Gain			320		
I _{LIM}	Peak Current Limit	T _j = 25°C	0.32	0.40	0.48	Α
T _D	Current Sense Delay to Turn-Off	I _D =0.2A			200	ns
Тв	Blanking Time				500	ns
Tonmin	Minimum Turn On Time				700	ns
PROTEC1	TION SECTION				•	
T _{SD}	Thermal Shutdown Temperature		140	170	-	°C
T _{HYST}	Thermal Shutdown Hysteresis			40		°C
V _{OVP}	Over Voltage Protection		38	42	46	V
SUPPLY (CURRENT SECTION					•
I _{CH}	Startup Charging Current			1		mA
	Start Up Charging Current in Thermal Shutdown	VCC=5V;				
ICHOFF		V _{DS} =100V			0.2	mA
		$T_j > T_{SD}$				
І ОР0	Operating Supply Current (Control Part Only) Switching	V _{COMP} = 0V		4.5		mA
l _{OP1}	Operating Supply Current (Control Part Only) Not Switching	V _{COMP} = 2V		3	5	mA

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BLOCK DIAGRAM



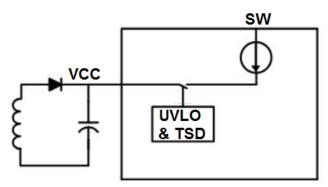
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DETAILED INFORMATION

Startup

This device includes a high voltage start up current source connected on the SW of the device. As soon as a voltage is applied on the input of the converter, this start up current source is activated and to charge the VCC capacitor as long as VCC is lower than VSTART. When reaching VSTART, the start up current source is cut off by UVLO&TSD and the device begins to operate by turning on and off its main power MOSFET. As the COMP pin does not receive any current from the opto-coupler, the device operates at full current capacity and the output voltage rises until reaching the regulation point where the secondary loop begins to send a current in the opto-coupler. At this point, the converter enters a regulated operation where the COMP pin receives the amount of current needed to deliver the right power on secondary side.

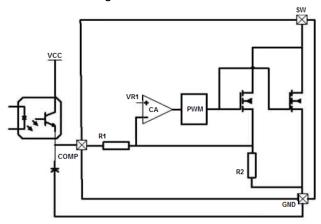
Fig 1. Startup circuit



Feedback

A feedback pin controls the operation of the device. Unlike conventional PWM control circuits which use a voltage input, the COMP pin is sensitive to current. The Fig 2. presents the internal current mode structure.

Fig 2. Feedback Circuit



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The Power MOSFET delivers a sense current which is proportional to the main current. R2 receives this current and the current coming from the COMP pin. The voltage across R2 VR2 is then compared to a fixed reference voltage. The MOSFET is switched off when VR2 equals the reference voltage.

Leading Edge Blanking (LEB)

At the instant the internal Sense FET is turned on, there usually exists a high current spike through the Sense FET, caused by the primary side capacitance and secondary side rectifier diode reverse recovery. Excessive voltage across the sense resistor would lead to false feedback operation in the current mode PWM control. To counter this effect, the device employs a leading edge blanking (LEB) circuit. This circuit inhibits the PWM comparator for a short time (typically 500ns) after the Sense FET is turned on.

Under Voltage Lock Out

Once fault condition occurs, switching is terminated and the Sense FET remains off. This causes VCC to fall. When VCC reaches the UVLO stop voltage, 8V, the protection is reset and the internal high voltage current source charges the VCC capacitor. When VCC reaches the UVLO start voltage, 14.5V, the device resumes its normal operation. In this manner, the auto-restart can alternately enable and disable the switching of the power Sense FET until the fault condition is eliminated.

Thermal Shutdown (TSD)

The Sense FET and the control IC are integrated in the same chip, making it easier for the control IC to detect the temperature of the Sense FET. When the temperature exceeds approximately 170°C, thermal shutdown is activated, the device turn off the Sense FET and the high voltage current source to charge VCC. The device will go back to work when the lower threshold temperature about 140°C is reached.

Over Voltage Protection (OVP)

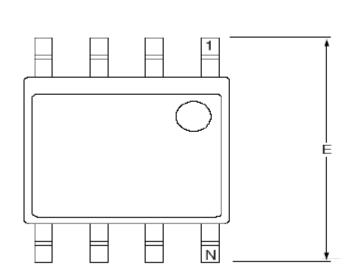
In case of malfunction in the secondary side feedback circuit, or feedback loop open caused by a defect of solder, the current through the opto-coupler transistor becomes almost zero. Because excess energy is provided to the output, the output voltage may exceed the rated voltage, resulting in the breakdown of the devices in the secondary side. In order to prevent this situation, an over voltage protection (OVP) circuit is employed. If VCC exceeds 42V, OVP circuit is activated resulting in termination of the switching operation. In order to avoid undesired activation of OVP during normal operation, VCC should be properly designed to be below 42V.

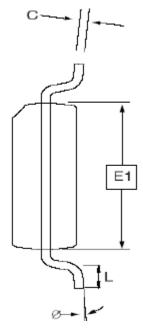
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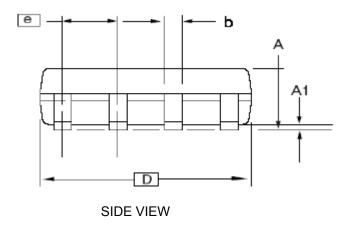
PACKAGE INFORMATION

Dimension in SOP8 Package (Unit: mm)





TOP VIEW



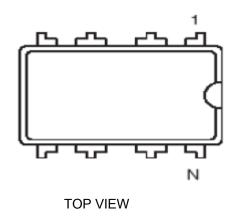
END VIEW

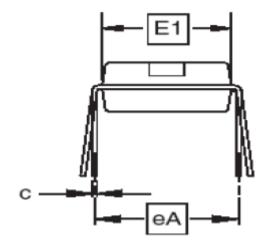
SYMBOL	MIN	NOM	MAX
Α	-	-	1.77
A1	0.08	0.18	0.28
В	0.44	-	0.53
С	0.21	-	0.26
D	4.70	4.90	5.10
Е	5.80	6.00	6.20
E1	3.70	3.90	4.10
Е		1.27BSC	
Ф	0	-	8°

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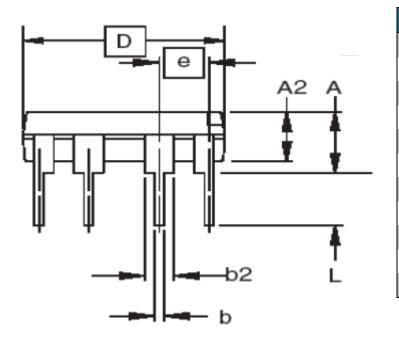


Dimension in DIP8 Package (Unit: mm)





END VIEW



SYMBOL	MIN	NOM	MAX
А	3.60	3.80	4.00
A2	3.10	3.30	3.50
b	0.44	-	0.53
B1		1.52BSC	
С	0.25	-	0.31
c1	0.24	0.25	0.26
D	9.05	9.25	9.45
E1	6.15	6.35	6.55
е		2.54BSC	
eA		7.62BSC	
L	3.00	-	-

SIDE VIEW

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